

**AMENDMENTS TO THE CLAIMS:**

- Claim 1. (Currently amended) A liquid crystal display device, comprising:  
a plurality of pixels arranged in a matrix form, each of said pixels  
comprising: including  
a pixel electrode formation area wherein a pixel electrode is formed; and  
a thin film transistor formation area wherein a thin film transistor is formed  
and connected to said pixel electrode, said thin film transistor comprising: having  
a semiconductor layer serving as a channel; ;  
a terminal formed to be connected to said pixel electrode; ;  
a passivation layer formed to cover said thin film transistor; and  
an organic insulating layer covering said passivation layer,  
wherein said pixel electrode formation area comprises a plurality of prism-shaped  
base posts, and an uneven layer formed on said plurality of prism-shaped base posts,  
wherein said semiconductor layer extends ~~being extended~~ from said channel toward  
said pixel electrode formation area beyond said terminal and terminated in said pixel  
electrode formation area to form a termination end that is aligned with a termination end of  
said passivation layer, and  
wherein said organic insulating layer covers ~~being elongated to cover~~ said termination  
ends of said semiconductor layer and said passivation layer.
- Claim 2. (Original) The device as claimed in claim 1, wherein said pixel electrode is  
connected to said terminal of said thin film transistor through a contact hole that is selectively  
formed in said organic insulating layer and said passivation layer.
- Claim 3. (New) The device as claimed in claim 1, wherein said uneven layer covers  
said plurality of prism-shaped base posts and is formed between said plurality of prism-  
shaped base posts.
- Claim 4. (New) The device as claimed in claim 1, wherein said pixel electrode  
comprises a reflection-type electrode which is formed on said uneven layer.

Claim 5. (New) The device as claimed in claim 6, wherein said pixel electrode comprises a shape which follows a contour of said uneven layer.

Claim 6. (New) The device as claimed in claim 1, wherein said uneven layer comprises a transparent photosensitive resist.

Claim 7. (New) The device as claimed in claim 1, wherein said pixel electrode comprises one of sputtered aluminum and sputtered silver.

Claim 8. (New) The device as claimed in claim 1, further comprising:  
a transparent insulating substrate, said plurality of prism-shaped base posts being formed on said transparent insulating substrate.

Claim 9. (New) The device as claimed in claim 8, wherein said thin film transistor further comprises a gate insulation film formed on said transparent insulating substrate.

Claim 10. (New) The device as claimed in claim 9, wherein said plurality of prism-shaped base posts comprise:  
an insulation film formed on said transparent substrate;  
a semiconductor film formed on said insulation layer; and  
an inorganic insulating film formed on said semiconductor layer.

Claim 11. (New) The device as claimed in claim 10, wherein said insulation film, said semiconductor film, and said inorganic insulating film are formed concurrently with a formation of said gate insulation film, said semiconductor layer and said passivation film in said thin film transistor, respectively.

Claim 12. (New) The device as claimed in claim 1, wherein said thin film transistor further comprises a drain electrode, said pixel electrode being connected to said drain electrode via a contact through hole formed in said uneven layer, and a contact through hole passing through said passivation layer.

Claim 13. (New) A thin film transistor array substrate for a liquid crystal display device, said thin film transistor substrate comprising:

- an insulating substrate;
- a plurality of data lines formed on said insulating substrate;
- a plurality of gate lines formed on said insulating substrate, such that areas bounded by said plurality of gate lines and said plurality of data lines define a plurality of pixels in said liquid crystal display device;
- a plurality of thin film transistors respectively formed on said insulating substrate in said plurality of pixels;
- a plurality of prism-shaped base posts formed adjacent to a thin film transistor in each of said plurality of pixels;
- an uneven layer formed on said plurality of prism-shaped base posts; and
- a pixel electrode formed on said uneven layer.

Claim 14. (New) The thin film transistor array substrate according to claim 13, wherein said thin film transistor comprises:

- a gate insulation layer formed on said transparent insulating substrate;
- a semiconductor layer formed on said gate insulation layer; and
- a passivation layer formed on said semiconductor layer.

Claim 15. (New) The device as claimed in claim 14, wherein said plurality of prism-shaped base posts comprises:

- an insulation film formed on said transparent substrate;
- a semiconductor film formed on said insulation layer; and
- an inorganic insulating film formed on said semiconductor layer.

Claim 16. (New) The device as claimed in claim 15, wherein said insulation film, said semiconductor film, and said inorganic insulating film are formed concurrently with a formation of said gate insulation layer, said semiconductor layer and said passivation layer in said thin film transistor, respectively.

Claim 17. (New) A method of forming a thin film transistor array substrate for a liquid crystal display device, comprising:

- forming a plurality of data lines on a insulating substrate;
- forming a plurality of gate lines on said insulating substrate, such that areas bounded by said plurality of gate lines and said plurality of data lines define a plurality of pixels in said liquid crystal display device;
- forming a plurality of thin film transistors respectively on said insulating substrate in said plurality of pixels;
- forming a plurality of prism-shaped base posts adjacent to a thin film transistor in each of said plurality of pixels;
- forming an uneven layer on said plurality of prism-shaped base posts; and
- forming a pixel electrode formed on said uneven layer.

Claim 18. (New) The method according to claim 17, wherein said forming said plurality of thin film transistors comprises:

- forming a gate insulation layer on said transparent insulating substrate;
- forming a semiconductor layer on said gate insulation layer; and
- forming a passivation layer on said semiconductor layer.

Claim 19. (New) The device as claimed in claim 18, wherein said forming said plurality of prism-shaped base posts comprises:

- forming an insulation film on said transparent substrate;
- forming a semiconductor film on said insulation layer; and
- forming an inorganic insulating film on said semiconductor layer.

Claim 20. (New) The device as claimed in claim 19, wherein said forming said insulation film, forming said semiconductor film, and forming said inorganic insulating film are performed concurrently with said forming said gate insulation layer, forming said semiconductor layer and forming said passivation layer in said thin film transistor, respectively.